

2SB1593

Silicon PNP epitaxial planar type

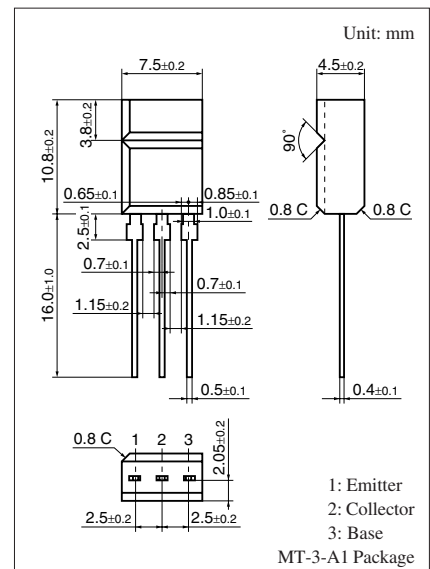
For low-frequency output amplification

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Allowing automatic insertion with radial taping

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

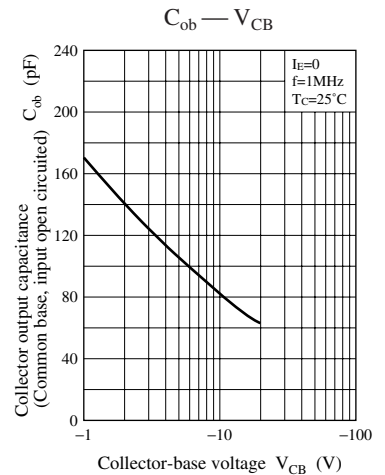
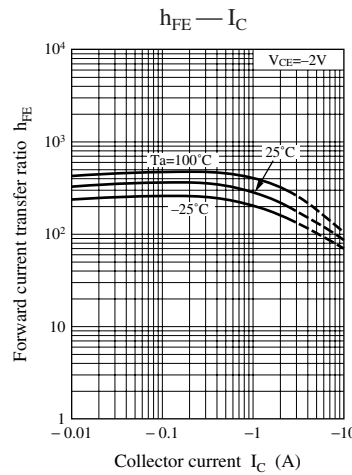
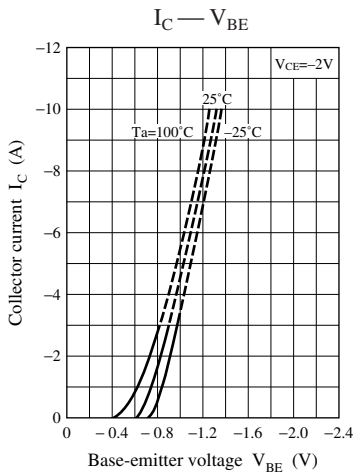
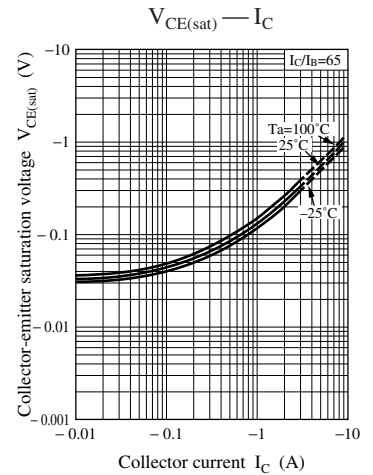
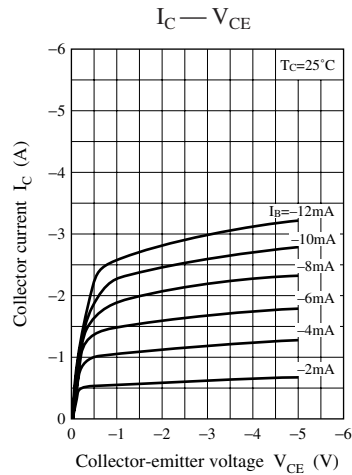
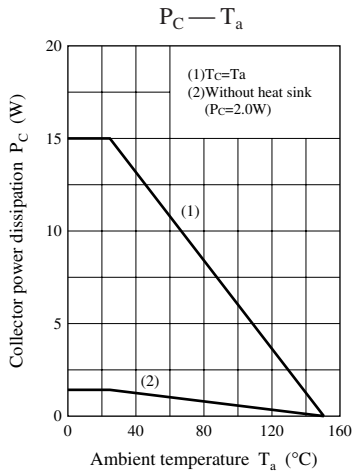
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-29	V
Collector-emitter voltage (Resistor between B and E)	V_{CER}	-29	V
Collector-emitter voltage (Base open)	V_{CEO}	-20	V
Emitter-base voltage (Collector open)	V_{EBO}	-11	V
Collector current	I_C	-3	A
Peak collector current	I_{CP}	-10	A
Collector power dissipation	P_C	1.5	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10 \mu\text{A}$, $I_E = 0$	-29			V
Collector-emitter voltage (Resistor between B and E)	V_{CER}	$I_C = -1 \text{ mA}$, $R_{BE} = 10 \text{ k}\Omega$	-29			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -1 \text{ mA}$, $I_B = 0$	-20			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}$, $I_C = 0$	-11			V
Forward current transfer ratio	h_{FE}	$V_{CE} = -2 \text{ V}$, $I_C = -2.6 \text{ A}$	100		450	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2.6 \text{ A}$, $I_B = -40 \text{ mA}$		-0.3	-0.5	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}$, $I_E = 50 \text{ mA}$, $f = 200 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		110	150	pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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